PROCESS **CPD64**

Low Leakage Diode

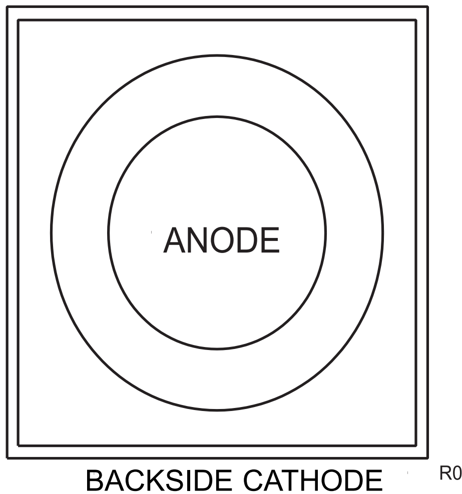
Low Leakage Diode Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	17.5 x 17.5 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	8.0 MILS DIAMETER
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

36,890

PRINCIPAL DEVICE TYPES

CMPD3003
1N3595

145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

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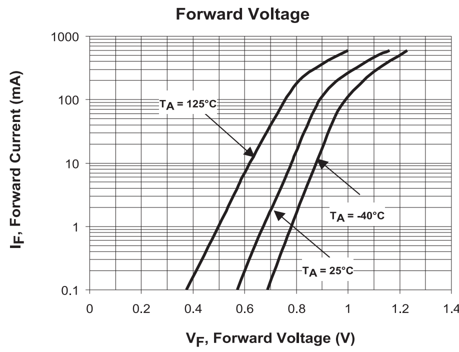
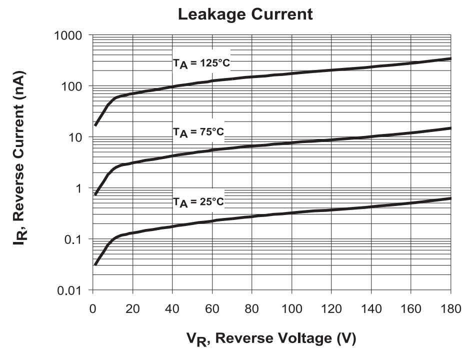
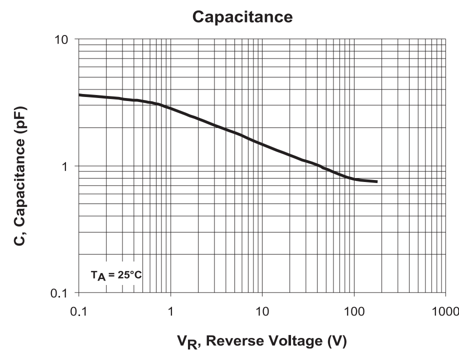
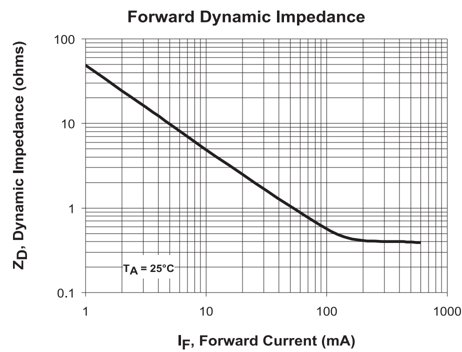
PROCESS CPD64

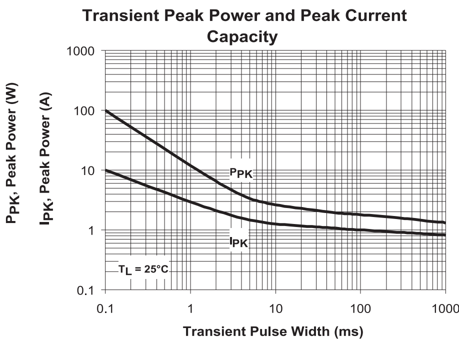
Typical Electrical Characteristics

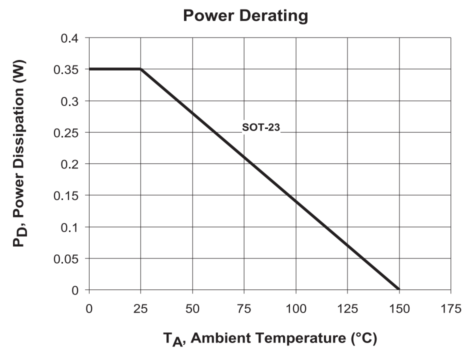












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